

TC1219/TC1220

Switched Capacitor Voltage Converters with Shutdown in SOT Packages

Features

- Charge Pumps in 6-Pin SOT-23A Package
- >95% Voltage Conversion Efficiency
- Voltage Inversion and/or Doubling
- Operates from +2.5V to +5.5V
- Up to 25mA Output Current
- Only Two External Capacitors Required
- Low Power Consumption
- Power-Saving Shutdown Mode
- TC1220 Compatible with 1.8V Logic Systems

Applications

- LCD Panel Bias
- Cellular Phones
- · Pagers
- PDAs, Portable Dataloggers
- Battery-Powered Devices

Device Selection Table

| Part Number | Package | Osc. Freq. (kHz) | Operating Temp. Range |
|----------------|---------------|------------------------|-----------------------------|
| TC1219ECH | 6-Pin SOT-23A | 12 | -40°C to +85°C |
| TC1220ECH | 6-Pin SOT-23A | 35 | -40°C to +85°C |

Package Type



General Description

The TC1219/TC1220 are CMOS "charge-pump" voltage converters in ultra-small 6-Pin SOT-23A packages. They invert and/or double an input voltage which can range from +2.5V to +5.5V. Conversion efficiency is typically >95%. Switching frequency is 12kHz for the TC1219, 35kHz for the TC1220. When the shutdown pin is held at a logic low, the device goes into a very low power mode of operation, consuming less than 1 μ A of supply current.

External component requirement is only two capacitors for standard voltage inverter applications. With a few additional components a positive doubler can also be built. All other circuitry, including control, oscillator, power MOSFETs are integrated on-chip. Typical supply currents are $60\mu A$ (TC1219), $115\mu A$ (TC1220).

All devices are available in 6-pin SOT-23A surface mount packages.

Functional Block Diagram



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings*

| Input Voltage (V _{IN} to GND) | +6.0V, -0.3V |
|---|---------------|
| Output Voltage (OUT to GND) | 6.0V, +0.3V |
| Current at OUT Pin | 50mA |
| Short-Circuit Duration - OUT to GND | Indefinite |
| Power Dissipation ($T_A \le 70^{\circ}C$) | |
| 6-Pin SOT-23A | 240mW |
| Operating Temperature Range | 40°C to +85°C |
| Storage Temperature (Unbiased)6 | E°C to 1150°C |

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

TC1219/TC1220 ELECTRICAL SPECIFICATIONS

Electrical Characteristics: $T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{IN} = +5V$, $C1 = C2 = 10\mu$ F, (TC1219), $C1 = C2 = 3.3\mu$ F (TC1220), $T_A = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | Min | Тур | Max | Units | Device | Test Conditions |
|-------------------|-------------------------------|------------------------|-----------|------------|-------|------------------|---|
| I _{DD} | Supply Current | | 60 115 | 115 325 | μA | TC1219 TC1220 | |
| I _{SHDN} | Shutdown Supply Current | _ | 0.1 | 1.0 | μA | | $\overline{\text{SHDN}} = \text{GND}, V_{\text{IN}} = 5V \text{ (Note 2)}$ |
| V _{MIN} | Minimum Supply Voltage | 2.5 | _ | _ | V | | $R_{LOAD} = 1k\Omega$ |
| V _{MAX} | Maximum Supply Voltage | _ | _ | 5.5 | V | | $R_{LOAD} = 1k\Omega$ |
| F _{OSC} | Oscillator Frequency | 6 19 | 12 35 | 20 56.3 | kHz | TC1219 TC1220 | |
| V _{IH} | SHDN Input Logic High | — 1.5 1.8 1.5 | | | V | TC1219 TC1220 | $R_{LOAD} = \infty$ $V_{IN} = V_{MIN} \text{ to } 3V$ $V_{IN} = >3V \text{ to } V_{MAX}$ $V_{IN} = V_{MIN} \text{ to } V_{MAX}$ |
| V _{IL} | SHDN Input Logic Low | _ | _ | 0.5 | V | | $V_{IN} = V_{MIN}$ to V_{MAX} |
| P _{EFF} | Power Efficiency | | 96 95 | | % | | $R_{LOAD} = 1k\Omega$ |
| V_{EFF} | Voltage Conversion Efficiency | 95 | 99.9 | _ | % | | $R_{LOAD} = \infty$ |
| R _{OUT} | Output Resistance | | 25 | 65 | Ω | TC1219/TC1220 | $I_{LOAD} = 0.5$ mA to 25mA (Note 1) |

Note 1: Capacitor contribution is approximately 20% of the output impedance [ESR = 1/ pump frequency x capacitance].

2: V_{IN} is guaranteed to be disconnected from OUT when the converter is in shutdown.

2.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 2-1.

TABLE 2-1: PIN FUNCTION TABLE

| Pin No. (6-Pin SOT-23A) | Symbol | Description | |
|----------------------------|-----------------|--|--|
| 1 | OUT | Inverting charge pump output. | |
| 2 | V _{IN} | Positive power supply input. | |
| 3 | C | Commutation capacitor negative terminal. | |
| 4 | GND | Ground. | |
| 5 | SHDN | Shutdown input (active low). | |
| 6 | C+ | Commutation capacitor positive terminal. | |

3.0 DETAILED DESCRIPTION

The TC1219/TC1220 charge pump converters invert the voltage applied to the V_{IN} pin. Conversion consists of a two-phase operation (Figure 3-1). During the first phase, switches S2 and S4 are opened and S1 and S3 are closed. During this time, C1 charges to the voltage on V_{IN} and load current is supplied from C2. During the second phase, S2 and S4 are closed, and S1 and S3 are opened. This action connects C1 across C2, restoring charge to C2.



4.0 APPLICATIONS INFORMATION

4.1 Output Voltage Considerations

The TC1219/TC1220 perform voltage conversion but do not provide *regulation*. The output voltage will droop in a linear manner with respect to load current. The value of this equivalent output resistance is approximately 25Ω nominal at $+25^{\circ}$ C and $V_{IN} = +5V$. V_{OUT} is approximately -5V at light loads, and droops according to the equation below:

 $V_{DROP} = I_{OUT} \times R_{OUT}$ $V_{OUT} = -(V_{IN} - V_{DROP})$

4.2 Charge Pump Efficiency

The overall power efficiency of the charge pump is affected by four factors:

- 1. Losses from power consumed by the internal oscillator, switch drive, etc. (which vary with input voltage, temperature and oscillator frequency).
- I²R losses due to the on-resistance of the MOSFET switches on-board the charge pump.
- 3. Charge pump capacitor losses due to effective series resistance (ESR).
- 4. Losses that occur during charge transfer (from the commutation capacitor to the output capacitor) when a voltage difference between the two capacitors exists.

Most of the conversion losses are due to factors (2) and (3) above. These losses are given by Equation 4-1(b).

EQUATION 4-1:

b) where ROUT = [1 / [fOSC(C1)] + 8RSWITCH + 4ESRC1 + ESRC2]

The $1/(f_{OSC})(C1)$ term in Equation 4-1(b) is the effective output resistance of an ideal switched capacitor circuit (Figure 4-1 and Figure 4-2). The value of R_{SWITCH} can be approximated at 0.5 Ω for the TC1219/TC1220.

The remaining losses in the circuit are due to factor (4) above, and are shown in Equation 4-2. The output voltage ripple is given by Equation 4-3.

EQUATION 4-2:

PLOSS(4) = [(0.5)(C1)(VIN² - VOUT²) + (0.5) $(C2)(VRIPPLE² - 2VOUT VRIPPLE)] \times fOSC$

EQUATION 4-3:

 $V_{RIPPLE} = [I_{OUT} / 2 x (f_{OSC}) (C2)] + 2 (I_{OUT}) (ESR_{C2})$

FIGURE 4-1: IDEAL SWITCHED CAPACITOR MODEL





EQUIVALENT OUTPUT RESISTANCE



4.3 Capacitor Selection

In order to maintain the lowest output resistance and output ripple voltage, it is recommended that low ESR capacitors be used. Additionally, larger values of C1 will lower the output resistance and larger values of C2 will reduce output ripple. (Equation 4-1(b) and Equation 4-3).

Table 4-1 shows various values of C1 and the corresponding output resistance values @ +25°C. It assumes a 0.1 Ω ESR_{C1} and 2 Ω R_{SWITCH}. Table 4-2 shows the output voltage ripple for various values of C2. The V_{RIPPLE} values assume 10mA output load current and 0.1 Ω ESR_{C2}.

TABLE 4-1:OUTPUT RESISTANCE VS.C1 (ESR = 0.1Ω)

| C1 (μF) | TC1219 R _{OUT} (Ω) | TC1220 R _{OUT} (Ω) |
|---------|--------------------------------|--------------------------------|
| 1 | 100 | 45 |
| 3.3 | 42 | 25 |
| 10 | 25 | 19.4 |
| 30 | 19.3 | 17.5 |

TABLE 4-2:OUTPUT VOLTAGE RIPPLE
VS. C2 (ESR = 0.1Ω)
I
OUT 10mA

| C2 (μF) | TC1219 V _{RIPPLE} (mV) | TC1220 V _{RIPPLE} (mV) |
|---------|------------------------------------|------------------------------------|
| 1 | 419 | 145 |
| 3.3 | 128 | 45 |
| 10 | 44 | 16 |
| 30 | 16 | 7 |

4.4 Input Supply Bypassing

The V_{IN} input should be capacitively bypassed to reduce AC impedance and minimize noise effects due to the internal switching of the device The recommended capacitor depends on the configuration of the TC1219/TC1220.

4.5 Shutdown Input

The TC1219/TC1220 is enabled when \overline{SHDN} is high, and disabled when \overline{SHDN} is low. This input cannot be allowed to float. (If \overline{SHDN} is not required, see the TCM828/829 data sheet.) The \overline{SHDN} input can be only driven to 0.5V above V_{IN} to avoid significant current flows.

4.6 Voltage Inverter

The most common application for charge pump devices is the inverter (Figure 4-3). This application uses two external capacitors: C1 and C2 (plus a power supply bypass capacitor, if necessary). The output is equal to $-V_{IN}$ plus any voltage drops due to loading. Refer to Table 4-1 and Table 4-2 for capacitor selection.

FIGURE 4-3: VOLTAGE INVERTER TEST CIRCUIT



4.7 Cascading Devices

Two or more TC1219/TC1220 can be cascaded to increase output voltage (Figure 4-4). If the output is lightly loaded, it will be close to $(-2 \times V_{IN})$ but will droop at least by R_{OUT} of the first device multiplied by the I_Q of the second. It can be seen that the output resistance rises rapidly for multiple cascaded devices.

4.8 Paralleling Devices

To reduce the value of R_{OUT} , multiple TC1219/ TC1220's can be connected in parallel (Figure 4-5). The output resistance will be reduced by a factor of N where N is the number of TC1219/TC1220. Each device will require its own pump capacitor (C1), but all devices may share one reservoir capacitor (C2). However, to preserve ripple performance the value of C2 should be scaled according to the number of paralleled TC1219/TC1220.

FIGURE 4-4: CASCADING MULTIPLE DEVICES TO INCREASE OUTPUT VOLTAGE



FIGURE 4-5: PARALLELING MULTIPLE DEVICES TO REDUCE OUTPUT RESISTANCE



4.9 Voltage Doubler/Inverter

Another common application of the TC1219/TC1220 is shown in Figure 4-6. This circuit performs two functions in combination. C1 and C2 form the standard inverter circuit described previously. C3 and C4 plus the two diodes form the voltage doubler circuit. C1 and C3 are the pump capacitors and C2 and C4 are the reservoir capacitors. Because both sub-circuits rely on the same switches if either output is loaded, both will droop toward GND. Make sure that the total current drawn from both the outputs does not total more than 40mA.

4.10 Diode Protection for Heavy Loads

When heavy loads require the OUT pin to sink large currents being delivered by a positive source, diode protection may be needed. The OUT pin should not be allowed to be pulled above ground. This is accomplished by connecting a Schottky diode (1N5817) as shown in Figure 4-7.

4.11 Layout Considerations

As with any switching power supply circuit good layout practice is recommended. Mount components as close together as possible to minimize stray inductance and capacitance. Noise leakage into other circuitry can be minimized with the use of a large ground plane.





FIGURE 4-7: HIGH V– LOAD CURRENT



5.0 **TYPICAL CHARACTERISTICS**

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.



Circuit of Figure 4-3, V_{IN} = +5V, C1 = C2 = C3, T_A = 25°C unless otherwise noted.

3.5

SUPPLY VOLTAGE (V)

TC1219

4.5

10

9

8

-40

5.5

-20

20

TEMPERATURE (°C)

0

40 60 80

50

40

30

20

10

0

2.5

60

40

80

30

25

20

-40

-20

0 20

TEMPERATURE (°C)

PUMP

TYPICAL CHARACTERISTICS (CONTINUED)



6.0 PACKAGING INFORMATION

6.1 Package Marking Information



① & ② = part number code + temperature range (two-digit code)

| TC1219/TC1220 | <u>Code</u> |
|---------------|-------------|
| TC1219ECH | AM |
| TC1220ECH | AN |

ex: 1219ECH =A M ⊖ ⊖

③ represents year and quarter code

④ represents production lot ID code

6.2 Taping Form



6.3 Package Dimensions



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TC1219/TC1220

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